## NSN 5961-01-089-2143

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-089-2143 **Inclosure Material:** Metal **Overall Length:** 1.646 inches **Overall Diameter:** 0.650 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Overall Width Across Flats:** 0.562 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 15.0 repetitive peak reverse voltage **Current Rating Per Characteristic:** 175.00 amperes forward current, total rms torr **Power Rating Per Characteristic:** 20.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Test Data Document:** 24930-g390165 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:** No

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